

**High purity silicon carbide powders for semiconductor and electronic applications.**

High purity silicon carbide produced by the Acheson process for semiconductor and electronic applications. Particularly suitable for PVT crystal growth for SiC wafer manufacturing.

**Typical Chemistry**

| Char. description     | Unit                | Value |
|-----------------------|---------------------|-------|
| Free C                | %                   | 0,01  |
| Free Si               | %                   | 0,05  |
| Total O <sub>2</sub>  | %                   | 0,05  |
| Size Instrument       | Malvern Mastersizer |       |
| Size d10%             | µm                  | 260   |
| Size d50%             | µm                  | 150   |
| Size d90%             | µm                  | 90    |
| ICP Slurry (unsieved) |                     |       |
| Al                    | ppm                 | 170   |
| Fe                    | ppm                 | 60    |
| Ni                    | ppm                 | 35    |
| V                     | ppm                 | 35    |
| Ca                    | ppm                 | 10    |
| Ti                    | ppm                 | 35    |
| Zr                    | ppm                 | 5     |

**Analytical Procedures:** All measurement is in accordance to FEPA, ANSI or JIS, or other methods in agreement with customers.

**Packaging:** 25 kg paper bags